

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S3	163	alwan.in.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/23 16:14
S4	16	"5240558"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/15 08:05
S5	5	"2002100609"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/15 08:05
S6	390	216/11.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/24 07:12
S8	1	"08964206"	US-PGPUB; USPAT; USOCR	OR	ON	2007/05/23 16:34
S9	877	216/24.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/24 07:12
S10	62	216/25.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/24 07:17

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S11	127	216/42.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/24 07:22
S12	3	"20010016235"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/24 07:28
S13	10490	polystyrene same (ball or sphere or bead or shape or circle or diameter) and (mask or shield or resist or etch adj stop)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/24 15:54
S14	1651	polystyrene same (ball or sphere or bead or shape or circle or diameter) same (mask or shield or resist or etch adj stop)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/24 08:06
S15	40	"6504180"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/24 08:07
S16	3	"2001014426"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/24 08:08
S17	0	"2001/014426"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/24 08:08

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S18	68	(alwan and james).in.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/24 08:35
S19	311	("aluminum gallium indium nitride") or ("aluminum gallium indium phosphite") or ("aluminum gallium indium phosphate")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/29 16:00
S20	138	((("aluminum gallium indium nitride") or ("aluminum gallium indium phosphite") or ("aluminum gallium indium phosphate"))) and (mask\$4 or resist or shield or etch adj stop or pattern\$4 or roughen\$4)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/24 08:54
S21	173	S19 not S20	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/24 08:54
S22	551	("aluminum gallium indium phosphide")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/24 09:05
S23	540	("aluminum gallium indium phosphide") not S19	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/24 09:05
S26	152	"5391259"	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2007/05/24 13:45
S27	69	S24 and (nanometer or nm or micron)	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2007/05/24 14:02

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S28	69	S24 and (nanometer or nm or micron or ".mu.m")	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2007/05/24 14:03
S29	71	S24 and (nanometer or nm or micron or "mu.m")	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2007/05/24 16:18
S30	8	((("aluminum gallium indium nitride") or ("aluminum gallium indium phosphite") or ("aluminum gallium indium phosphate"))) same ((emitter or cathode) with material)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/24 14:15
S31	9	((("aluminum gallium indium nitride") or ("aluminum gallium indium phosphite") or ("aluminum gallium indium phosphate"))) same (emitter or cathode)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/24 14:29
S32	11	"5574745"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/24 14:28
S34	9	((("aluminum gallium indium phosphite") or ("aluminum gallium indium phosphate") or ("aluminum gallium indium phosphide"))) same (emitter or cathode)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/24 14:32
S35	102	((("aluminum gallium indium phosphite") or ("aluminum gallium indium phosphate") or ("aluminum gallium indium phosphide") or AlGaInP) same (emitter or cathode)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/24 14:44
S36	12	(AlGaInP or AlGaInN) and "CH.sub.4" and "H.sub.2"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/24 15:55

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S37	16	"5240558"	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2007/05/24 16:17
S38	6	(nanometer or nm or micron or "mu.m") same (etch\$4 near2 depth) and (field adj emitter adj tip)	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2007/05/24 16:23
S39	19666	pattern\$4 and aspect adj ratio and (depth or width) and etch\$4	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2007/05/24 16:23
S40	1372142	(nanometer or nm or micron or "mu.m") pattern\$4 and aspect adj ratio and (depth or width) and etch\$4	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2007/05/25 07:24
S41	16770	(nanometer or nm or micron or "mu.m") and pattern\$4 and aspect adj ratio and (depth or width) and etch\$4	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2007/05/24 16:24
S42	2471	(nanometer or nm or micron or "mu.m") and pattern\$4 and aspect adj ratio and (depth or width) and etch\$4 and fed	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2007/05/25 07:20
S43	2541	(width or height or diameter) same surface adj (feature or structure) and etch\$4	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2007/05/25 07:24
S44	2671	(nanometer or nm or micron or "mu.m") and (width or height or diameter or depth) same surface adj (feature or structure) and etch\$4	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2007/05/25 08:13
S45	2671	(nanometer or nm or micron or "mu.m") and ((width or height or diameter or depth) same surface adj (feature or structure) and etch\$4)	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2007/05/25 12:13
S48	1170	etch\$ near2 depth with (nanometer or nm or micron or "mu.m") and aspect adj ratio	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2007/05/25 12:12
S49	155	emitter adj tips with (nanometer or nm or micron or "mu.m") and etch\$4	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2007/05/29 07:51

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S50	337	(semiconductor near3 electrode) with (nanometer or nm or micron or "mu.m") and etch\$4 and polysilicon	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2007/05/29 08:01
S51	160339	("50" or fifty) adj (nanometer or nm) etch\$4 and polysilicon	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2007/05/29 08:02
S52	871	((("50" or fifty) adj (nanometer or nm)) with (height or depth) and etch\$4 and polysilicon	US-PGPUB; USPAT; JPO; DERWENT	OR	ON	2007/05/29 08:03
S53	628	(AlGaInP or ("aluminum gallium indium phosphite") or ("aluminum gallium indium phosphate")) and bandgap	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/29 15:37
S54	262	(AlGaInP or ("aluminum gallium indium phosphite") or ("aluminum gallium indium phosphate")) same bandgap	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/29 15:37
S55	25	((("aluminum gallium indium nitride") or (AlGaInN)) same bandgap same (nm or nanometer)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/29 16:03
S56	77	((("aluminum gallium indium nitride") or (AlGaInN)) same bandgap	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/29 16:10
S57	224	((("aluminum gallium indium nitride") or (AlGaInN)) same blue	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/29 16:10

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S58	14	benefit near (icp or inductively adj coupled adj plasma)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/30 07:04
S59	7	benefit near3 (icp or inductively adj coupled adj plasma) and etch\$4	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/30 07:08
S60	40	"3739217"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/30 07:09
S61	95	"4407695"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/30 07:09
S62	64	"5256587"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/30 07:10
S63	39	"6410942"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/30 07:10